

8-Input Data Selector/ Multiplexer with 3-State Outputs

High-Performance Silicon-Gate CMOS

MC74HC251A

The MC54/74HC251 is identical in pinout to the LS251. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

This device selects one of the eight binary Data Inputs, as determined by the Address Inputs. The Output Enable pin must be a low level for the selected data to appear at the outputs. If Output Enable is high, both the Y and the $\bar{Y}$ outputs are in the high-impedance state. This 3-state feature allows the HC251 to be used in bus-oriented systems.

The HC251 is similar in function to the HC251 which does not have 3-state outputs.

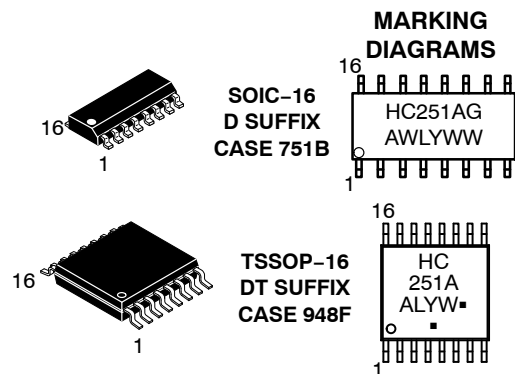
Features

- Output Drive Capability: 10 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2 to 6 V
- Low Input Current: 1 μ A
- High Noise Immunity Characteristic of CMOS Devices
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant



ON Semiconductor®

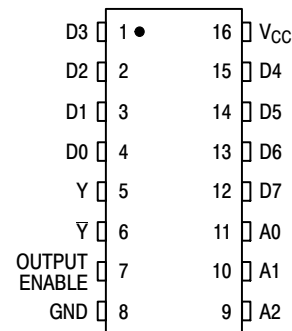
www.onsemi.com



A = Assembly Location
WL, L = Wafer Lot
YY, Y = Year
WW, W = Work Week
G or $\blacksquare$ = Pb-Free Package

(Note: Microdot may be in either location)

PIN ASSIGNMENT



ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.

MC74HC251A

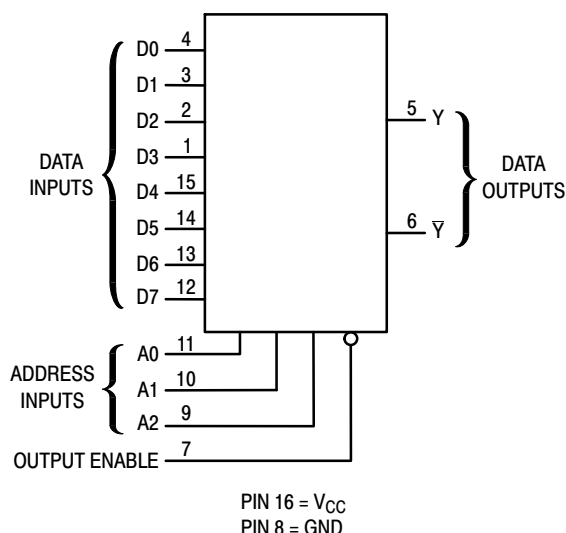


Figure 1. Logic Diagram

FUNCTION TABLE

Inputs				Outputs	
A2	A1	A0	Output Enabled	Y	$\bar{Y}$
X	X	X	H	Z	$\bar{Z}$
L	L	L	L	D0	$\bar{D0}$
L	L	H	L	D1	$\bar{D1}$
L	H	L	L	D2	$\bar{D2}$
L	H	H	L	D3	$\bar{D3}$
H	L	L	L	D4	$\bar{D4}$
H	L	H	L	D5	$\bar{D5}$
H	H	L	L	D6	$\bar{D6}$
H	H	H	L	D7	$\bar{D7}$

Z = high impedance

D0, D1, ..., D7 = the level of the respective D input.

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CC}	DC Supply Voltage (Referenced to GND)	-0.5 to + 7.0	V
V_{in}	DC Input Voltage (Referenced to GND)	-1.5 to $V_{CC} + 1.5$	V
V_{out}	DC Output Voltage (Referenced to GND)	-0.5 to $V_{CC} + 0.5$	V
I_{in}	DC Input Current, per Pin	± 25	mA
I_{out}	DC Output Current, per Pin	± 50	mA
I_{CC}	DC Supply Current, V_{CC} and GND Pins	± 75	mA
P_D	Power Dissipation in Still Air SOIC Package TSSOP Package	500 TBD	mW
T_{stg}	Storage Temperature	-65 to + 150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range $GND \leq (V_{in} \text{ or } V_{out}) \leq V_{CC}$. Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit	
V _{CC}	DC Supply Voltage (Referenced to GND)	2.0	6.0	V	
V _{in} , V _{out}	DC Input Voltage, Output Voltage (Referenced to GND)	0	V _{CC}	V	
T _A	Operating Temperature, All Package Types	−55	+125	°C	
t _r , t _f	Input Rise and Fall Time (Figure 2)	V _{CC} = 2.0 V V _{CC} = 4.5 V V _{CC} = 6.0 V	0 0 0	1000 500 400	ns

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

MC74HC251A

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

Symbol	Parameter	Test Conditions	V _{CC} V	Guaranteed Limit			Unit
				- 55 to 25°C	≤ 85°C	≤ 125°C	
V _{IH}	Minimum High-Level Input Voltage	V _{out} = 0.1 V or V _{CC} - 0.1 V I _{out} ≤ 20 μA	2.0 4.5 6.0	1.5 3.15 4.2	1.5 3.15 4.2	1.5 3.15 4.2	V
V _{IL}	Maximum Low-Level Input Voltage	V _{out} = 0.1 V or V _{CC} - 0.1 V I _{out} ≤ 20 μA	2.0 4.5 6.0	0.3 0.9 1.2	0.3 0.9 1.2	0.3 0.9 1.2	V
V _{OH}	Minimum High-Level Output Voltage	V _{in} = V _{IH} or V _{IL} I _{out} ≤ 20 μA	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V
		V _{in} = V _{IH} or V _{IL} I _{out} ≤ 4.0 mA I _{out} ≤ 5.2 mA	4.5 6.0	3.98 5.48	3.84 5.34	3.70 5.20	
V _{OL}	Maximum Low-Level Output Voltage	V _{in} = V _{IH} or V _{IL} I _{out} ≤ 20 μA	2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V
		V _{in} = V _{IH} or V _{IL} I _{out} ≤ 4.0 mA I _{out} ≤ 5.2 mA	4.5 6.0	0.26 0.26	0.33 0.33	0.40 0.40	
I _{in}	Maximum Input Leakage Current	V _{in} = V _{CC} or GND	6.0	± 0.1	± 1.0	± 1.0	μA
I _{OZ}	Maximum Three-State Leakage Current	Output in High-Impedance State V _{in} = V _{IL} or V _{IH} V _{out} = V _{CC} or GND	6.0	± 0.5	± 5.0	± 10	μA
I _{CC}	Maximum Quiescent Supply Current (per Package)	V _{in} = V _{CC} or GND I _{out} = 0 μA	6.0	8	80	160	μA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

MC74HC251A

AC ELECTRICAL CHARACTERISTICS (C_L = 50 pF, Input t_r = t_f = 6 ns)

Symbol	Parameter	V _{CC} V	Guaranteed Limit			Unit
			– 55 to 25°C	≤ 85°C	≤ 125°C	
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Input D to Output Y or $\bar{Y}$ (Figures 2, 3 and 6)	2.0 4.5 6.0	185 37 31	230 46 39	280 56 48	ns
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Input A to Output Y or $\bar{Y}$ (Figures 3 and 6)	2.0 4.5 6.0	205 41 35	255 51 43	310 62 53	ns
t _{PLZ} , t _{PHZ}	Maximum Propagation Delay, Output Enable to Output Y (Figures 5 and 7)	2.0 4.5 6.0	195 39 33	245 49 42	295 59 50	ns
t _{PZL} , t _{PZH}	Maximum Propagation Delay, Output Enable to Output Y (Figures 5 and 7)	2.0 4.5 6.0	145 29 25	180 36 31	220 44 38	ns
t _{PLZ} , t _{PHZ}	Maximum Propagation Delay, Output Enable to Output $\bar{Y}$ (Figures 5 and 7)	2.0 4.5 6.0	220 44 37	275 55 47	330 66 56	ns
t _{PZL} , t _{PZH}	Maximum Propagation Delay, Output Enable to Output $\bar{Y}$ (Figures 5 and 7)	2.0 4.5 6.0	150 30 26	190 38 33	225 45 38	ns
t _{TLH} , t _{THL}	Maximum Output Transition Time, Any Output (Figures 2 and 6)	2.0 4.5 6.0	75 15 13	95 19 16	110 22 19	ns
C _{in}	Maximum Input Capacitance	–	10	10	10	pF
C _{out}	Maximum Three-State Output Capacitance (Output in High-Impedance State)	–	15	15	15	pF

C _{PD}	Power Dissipation Capacitance (Per Package)	Typical @ 25°C, V _{CC} = 5.0 V	pF
		36	

PIN DESCRIPTIONS

INPUTS

D0, D1, ..., D7 (Pins 4, 3, 2, 1, 15, 14, 13, 12)

Data inputs. Data on one of these eight binary inputs may be selected to appear on the output.

CONTROL INPUTS

A0, A1, A2 (Pins 11, 10, 9)

Address inputs. The data on these pins are the binary address of the selected input (see the Function Table).

Output Enable (Pin 7)

Output Enable. This input pin must be at a low level for the selected data to appear at the outputs. If the Output Enable pin is high, both the Y and $\bar{Y}$ outputs are taken to the high-impedance state.

OUTPUTS

Y, $\bar{Y}$ (Pins 5, 6)

Data outputs. The selected data is presented at these pins in both true (Y output) and complemented ($\bar{Y}$ output) forms.

MC74HC251A

SWITCHING WAVEFORMS

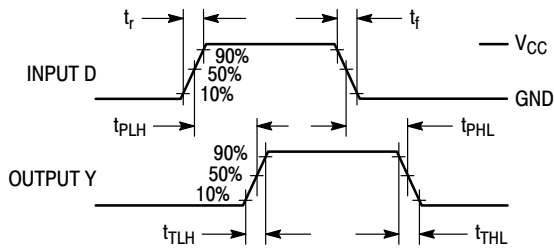


Figure 2.

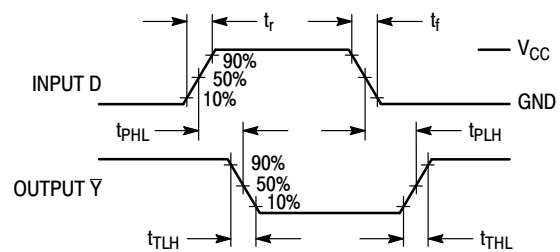


Figure 3.

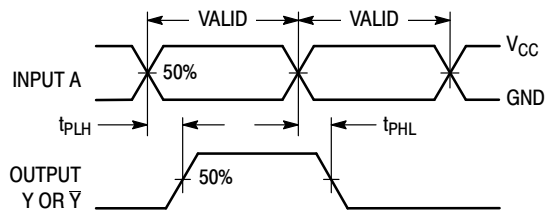


Figure 4.

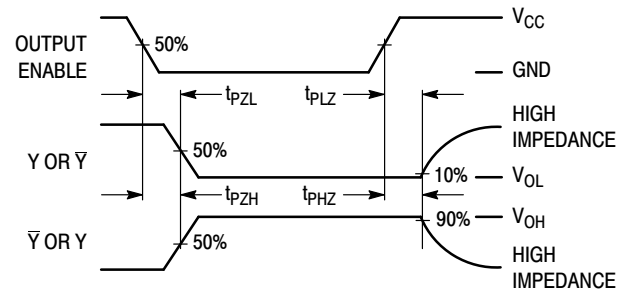
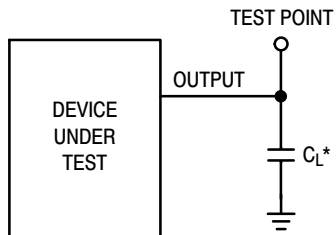


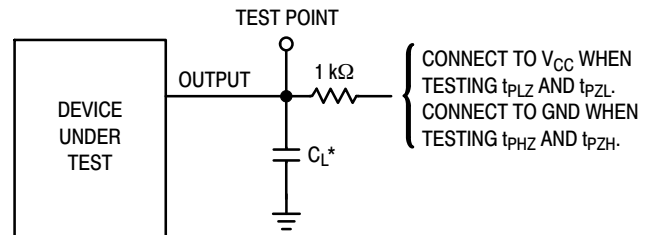
Figure 5.

TEST CIRCUITS



*Includes all probe and jig capacitance

Figure 6.



*Includes all probe and jig capacitance

Figure 7.

MC74HC251A

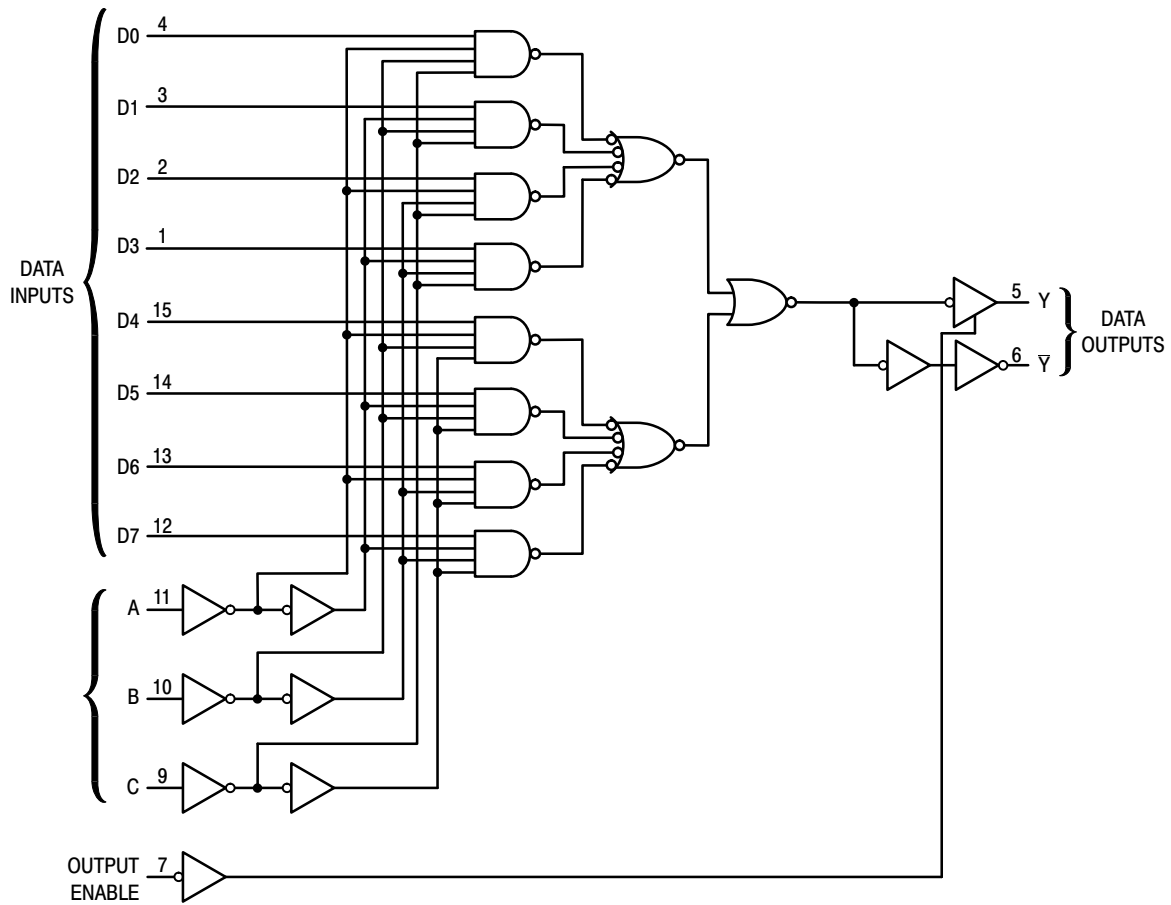


Figure 8. Expanded Logic Diagram

ORDERING INFORMATION

Device	Package	Shipping†
MC74HC251ADG	SOIC-16 (Pb-Free)	48 Units / Rail
MC74HC251ADR2G		2500 Tape & Reel
NLV74HC251ADR2G*		2500 Tape & Reel
MC74HC251ADTG	TSSOP-16 (Pb-Free)	96 Units / Rail
MC74HC251ADTR2G		2500 Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

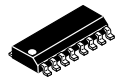
*NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

ON Semiconductor®

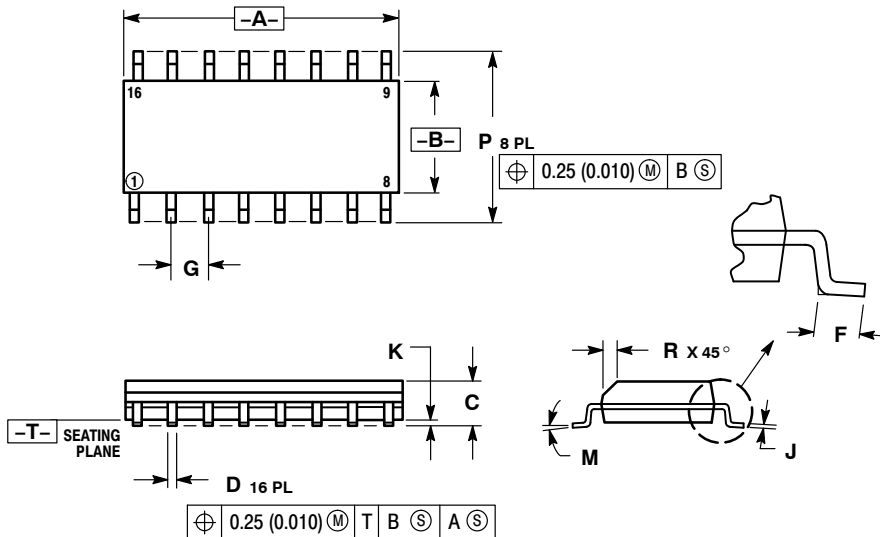
ON



SCALE 1:1

SOIC-16 CASE 751B-05 ISSUE K

DATE 29 DEC 2006



NOTES:

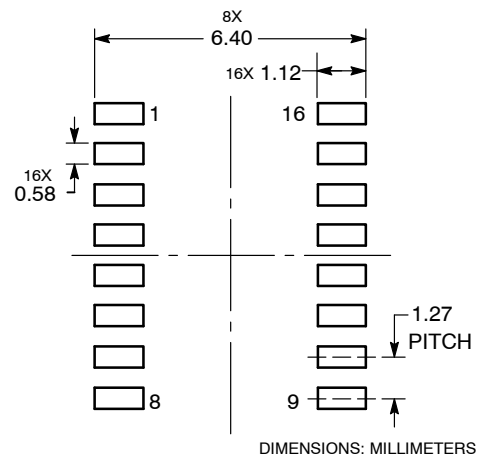
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	9.80	10.00	0.386	0.393
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
E	0.40	1.25	0.016	0.049
F	1.27 BSC		0.050 BSC	
G	0.19	0.25	0.008	0.009
H	0.10	0.25	0.004	0.009
I	0°	7°	0°	7°
J	5.80	6.20	0.229	0.244
K	0.25	0.50	0.010	0.019

STYLE 1:	STYLE 2:	STYLE 3:	STYLE 4:
PIN 1. COLLECTOR	PIN 1. CATHODE	PIN 1. COLLECTOR, DYE #1	PIN 1. COLLECTOR, DYE #1
2. BASE	2. ANODE	2. BASE, #1	2. COLLECTOR, #1
3. EMITTER	3. NO CONNECTION	3. EMITTER, #1	3. COLLECTOR, #2
4. NO CONNECTION	4. CATHODE	4. COLLECTOR, #1	4. COLLECTOR, #2
5. EMITTER	5. CATHODE	5. COLLECTOR, #2	5. COLLECTOR, #3
6. BASE	6. NO CONNECTION	6. BASE, #2	6. COLLECTOR, #3
7. COLLECTOR	7. ANODE	7. EMITTER, #2	7. COLLECTOR, #4
8. COLLECTOR	8. CATHODE	8. COLLECTOR, #2	8. COLLECTOR, #4
9. BASE	9. CATHODE	9. COLLECTOR, #3	9. BASE, #4
10. EMITTER	10. ANODE	10. BASE, #3	10. EMITTER, #4
11. NO CONNECTION	11. NO CONNECTION	11. EMITTER, #3	11. BASE, #3
12. EMITTER	12. CATHODE	12. COLLECTOR, #3	12. EMITTER, #3
13. BASE	13. CATHODE	13. COLLECTOR, #4	13. BASE, #2
14. COLLECTOR	14. NO CONNECTION	14. BASE, #4	14. EMITTER, #2
15. EMITTER	15. ANODE	15. EMITTER, #4	15. BASE, #1
16. COLLECTOR	16. CATHODE	16. COLLECTOR, #4	16. EMITTER, #1

STYLE 5:	STYLE 6:	STYLE 7:
PIN 1. DRAIN, DYE #1	PIN 1. CATHODE	PIN 1. SOURCE N-CH
2. DRAIN, #1	2. CATHODE	2. COMMON DRAIN (OUTPUT)
3. DRAIN, #2	3. CATHODE	3. COMMON DRAIN (OUTPUT)
4. DRAIN, #2	4. CATHODE	4. GATE P-CH
5. DRAIN, #3	5. CATHODE	5. COMMON DRAIN (OUTPUT)
6. DRAIN, #3	6. CATHODE	6. COMMON DRAIN (OUTPUT)
7. DRAIN, #4	7. CATHODE	7. COMMON DRAIN (OUTPUT)
8. DRAIN, #4	8. CATHODE	8. SOURCE P-CH
9. GATE, #4	9. ANODE	9. SOURCE P-CH
10. SOURCE, #4	10. ANODE	10. COMMON DRAIN (OUTPUT)
11. GATE, #3	11. ANODE	11. COMMON DRAIN (OUTPUT)
12. SOURCE, #3	12. ANODE	12. COMMON DRAIN (OUTPUT)
13. GATE, #2	13. ANODE	13. GATE N-CH
14. SOURCE, #2	14. ANODE	14. COMMON DRAIN (OUTPUT)
15. GATE, #1	15. ANODE	15. COMMON DRAIN (OUTPUT)
16. SOURCE, #1	16. ANODE	16. SOURCE N-CH

SOLDERING FOOTPRINT



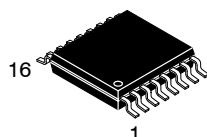
DIMENSIONS: MILLIMETERS

DOCUMENT NUMBER:	98ASB42566B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	SOIC-16	PAGE 1 OF 1

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

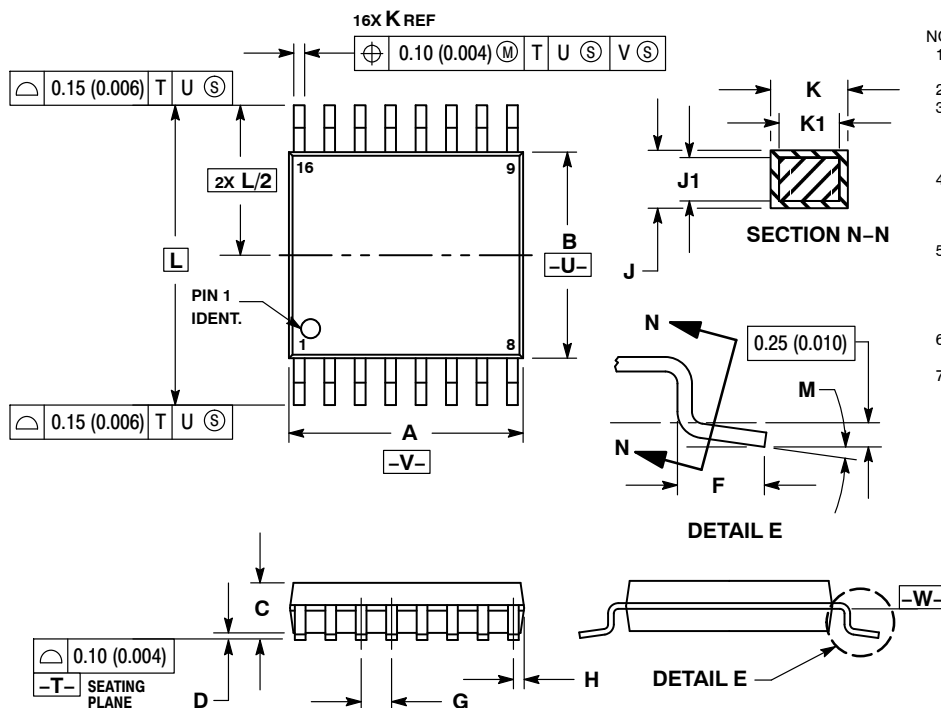
ON Semiconductor®



SCALE 2:1

TSSOP-16 CASE 948F-01 ISSUE B

DATE 19 OCT 2006

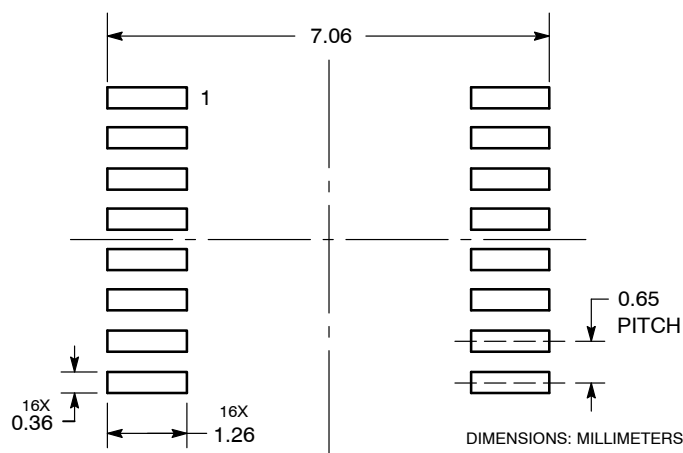


NOTES:

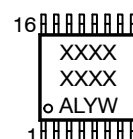
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.90	5.10	0.193	0.200
B	4.30	4.50	0.169	0.177
C	---	1.20	---	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
H	0.18	0.28	0.007	0.011
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0°	8°	0°	8°

SOLDERING FOOTPRINT



GENERIC MARKING DIAGRAM*



XXXX = Specific Device Code
A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week
G or ■ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present.

DOCUMENT NUMBER:	98ASH70247A	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	TSSOP-16	PAGE 1 OF 1

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

onsemi, **Onsemi**, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Email Requests to: orderlit@onsemi.com

onsemi Website: www.onsemi.com

TECHNICAL SUPPORT

North American Technical Support:

Voice Mail: 1 800-282-9855 Toll Free USA/Canada

Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative